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cdtimecodetraktorisomk2 Clash Royale Free Download Codes and Cheats Codes; Clash Royale Hack and Cheats Codes.1. Field of the Invention The present invention relates to the design of a semiconductor device having an integrated circuit device in a semiconductor substrate and a MOS capacitor in the device isolation film of the semiconductor substrate, and in particular, to a device isolation film technology for a semiconductor device such as a DRAM or the like. 2. Description of the Related Art A capacitor as a memory device for a DRAM (Dynamic Random Access Memory) in general comprises a capacitor insulation film, a capacitor electrode film, a capacitor contact hole and the like. In recent years, in order to increase the density of DRAMs, the area of the capacitor electrode is increased by reducing the capacitor contact hole. The capacitor contact hole is formed by removing the portions of the capacitor insulation film and the capacitor electrode film formed over the capacitor contact hole, and the capacitor insulation film and the capacitor electrode film are formed over the device isolation film. This process includes removing the capacitor insulation film and the capacitor electrode film over the device isolation film by RIE (Reactive Ion Etching) to form a recess, then filling the recess with a metal oxide film serving as the capacitor insulation film and a metal film serving as the capacitor electrode film, and polishing the surface of the metal film by CMP (Chemical Mechanical Polishing). In the above process, the capacitor insulation film, which is made of a metal oxide film, is composed of the metal oxide films having different etching rates from each other. Thus, the surface of the metal oxide film is polished, and a part of the metal oxide film on the side wall of the recess is removed, while the remaining part is left. Thus, it is difficult to obtain a flat capacitor electrode surface. As one of the measures for improving the flatness of the capacitor electrode surface, the capacitor contact hole is formed such that a height difference is given between the capacitor insulation film and the capacitor electrode film over the recess (Japanese Patent Laid-Open No. Hei 7-102946). In the above prior art, however, it is difficult to realize a high density DRAM by giving a height difference only between the capacitor insulation film and the capacitor electrode film. Accordingly, an object of the present invention is to provide a device isolation film technology for a semiconductor device having an integrated circuit device such as 2d92ce491b